## SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

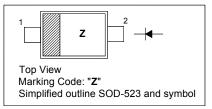
for rectifying small power applications

#### **Features**

- · Ultra small mold type
- · Low forward voltage
- High reliability

#### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings (T<sub>a</sub> = 25 °C)

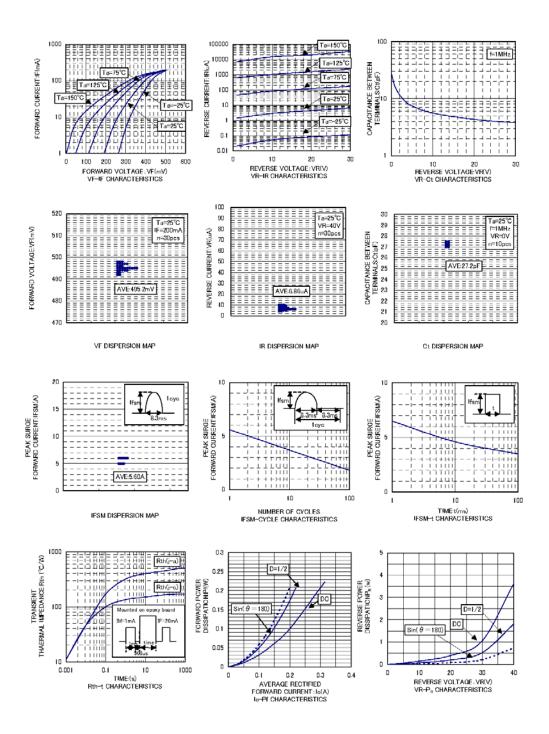
Parameter	Symbol	Value	Unit	
Repetitive Peak Reverse Voltage	$V_{RM}$	45	V	
Reverse Voltage	V <sub>R</sub>	40	V	
Mean Rectifying Current	Io	200	mA	
Peak Forward Surge Current (60Hz for Cyc.)	I <sub>FSM</sub>	1	Α	
Junction Temperature	T <sub>j</sub>	150	°C	
Storage Temperature Range	T <sub>s</sub>	- 55 to + 150	°C	

## Characteristics at T<sub>a</sub> = 25 °C

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 10 \text{ mA}$ at $I_F = 100 \text{ mA}$ at $I_F = 200 \text{ mA}$	V <sub>F</sub>	0.16 0.31 0.41	0.3 0.45 0.54	V
Reverse Current at $V_R = 10 \text{ V}$ at $V_R = 40 \text{ V}$	I <sub>R</sub>		20 90	μΑ

SEMTECH ELECTRONICS LTD. (Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)







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ISO/TS 16949: 2002 ISO 14001:2004 ISO 9001:2000 Certificate No. 05103 Certificate No. 7116 Certificate No. 0506098

#### **PACKAGE OUTLINE**

## Plastic surface mounted package; 2 leads

**SOD-523** 

